

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Numerical analysis of the influence of deep energy level traps in SiC Schottky structures

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SIC schottky diode rectifier bridge represented as the diffusion-welded stack

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SIC schottky diode rectifier bridge represented as the diffusion-welded stack

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Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe

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